

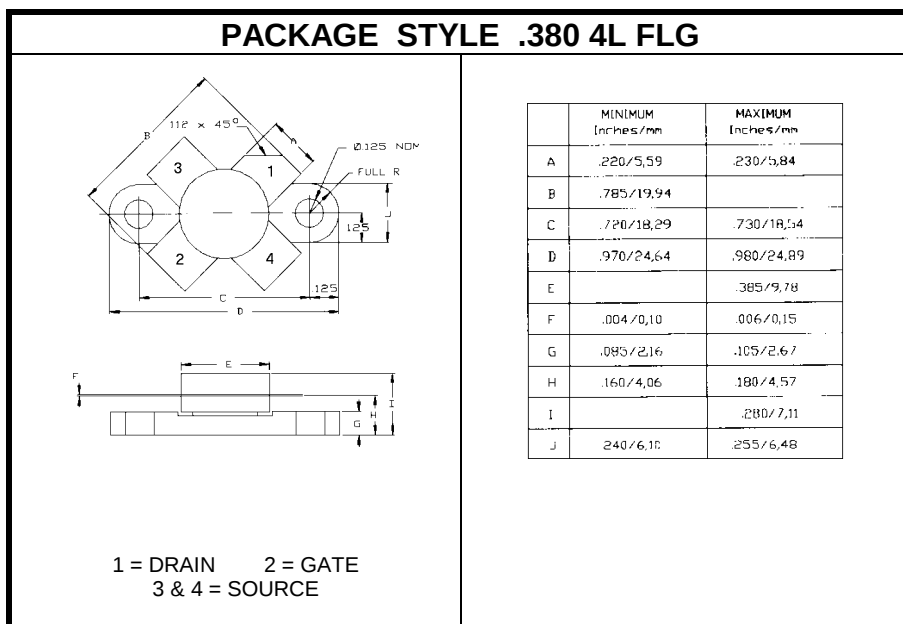
RF POWER FIELD-EFFECT TRANSISTOR

DESCRIPTION:

The **ASI MRF136** is a N-Channel Enhancement MOSFET, Designed for Wideband Large Signal Amplifier Applications up to 400 MHz.

MAXIMUM RATINGS

I_D	2.5 A
V_{DSS}	65 V
P_{DISS}	50 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.6 °C/W



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$I_D = 5.0 \text{ mA}$	$V_{GS} = 0 \text{ V}$		65			V
I_{DSS}	$V_{DS} = 28 \text{ V}$	$V_{GS} = 0 \text{ V}$				2.0	mA
I_{GSS}	$V_{DS} = 0 \text{ V}$	$V_{GS} = 40 \text{ V}$				1.0	μA
$V_{GS(th)}$	$I_D = 25 \text{ mA}$	$V_{DS} = 10 \text{ V}$		1.0	3.0	6.0	V
g_{fs}	$I_D = 250 \text{ mA}$	$V_{DS} = 10 \text{ V}$		250	400		mmhos
C_{iss} C_{oss} C_{rss}	$V_{DS} = 28 \text{ V}$	$V_{GS} = 0 \text{ V}$	$f = 1.0 \text{ MHz}$		24 5.5	25	pF
NF	$V_{DS} = 28 \text{ V}$	$I_D = 0.5 \text{ A}$	$f = 150 \text{ MHz}$		1.0		dB
G_{ps} η	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 25 \text{ mA}$	$P_{out} = 15 \text{ W}$	$f = 150 \text{ MHz}$	12 50	16 60		dB %
Ψ	$V_{DD} = 28 \text{ V}$ $I_{DQ} = 25 \text{ mA}$	$P_{out} = 15 \text{ W}$ VSWR 30:1 @ ALL PHASE ANGLES	$f = 150 \text{ MHz}$	NO DEGRADATION IN OUTPUT POWER			